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MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

MC14411

CMOS LSI

(LOW-POWER COMPLEMENTARY MOS)

BIT RATE GENERATOR

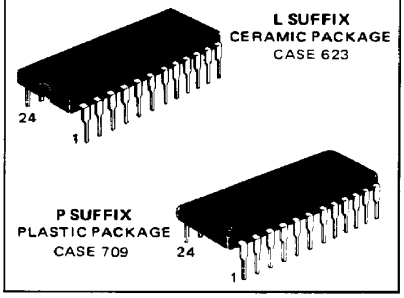
BIT RATE GENERATOR

The MC14411 bit rate generator is constructed with complementary MOS enhancement mode devices. It utilizes a frequency divider network to provide a wide range of output frequencies.

A crystal controlled oscillator is the clock source for the network. A two-bit address is provided to select one of four multiple output clock rates.

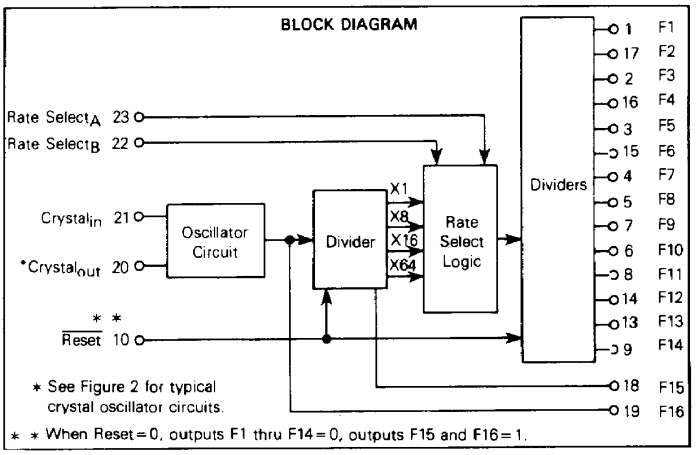
Applications include a selectable frequency source for equipment in the data communications market, such as teleprinters, printers, CRT terminals, and microprocessor systems.

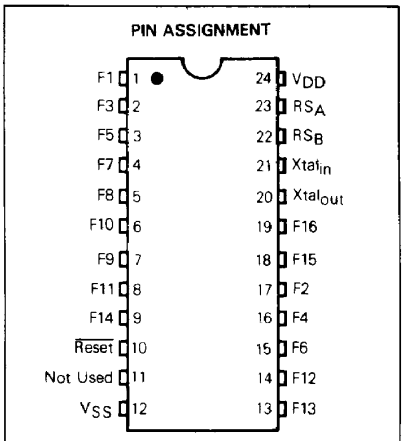
- Single 5.0 Vdc (±5%) Power Supply
- Internal Oscillator Crystal Controlled for Stability (1.8432 MHz)
- Sixteen Different Output Clock Rates
- 50% Output Duty Cycle
- Programmable Time Bases for One of Four Multiple Output Rates
- Buffered Outputs Compatible with Low Power TTL
- Noise Immunity = 45% of V_{DD} Typical
- Diode Protection on All Inputs
- External Clock May be Applied to Pin 21
- Internal Pullup Resistor on Reset Input



MAXIMUM RATINGS (Voltages referenced to V_{SS}, Pin 12.)

Rating	Symbol	Value	Unit
DC Supply Voltage Range	V_{DD}	5.25 to −0.5	V
Input Voltage, All Inputs	V_{in}	V_{DD} + 0.5 to V_{SS} − 0.5	V
DC Current Drain per Pin	I	10	mA
Operating Temperature Range	T_A	−40 to +85	°C
Storage Temperature Range	T_{stg}	−65 to +150	°C





This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields; however, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to this high impedance circuit. For proper operation it is recommended that V_{in} and V_{out} be constrained to the range $V_{SS} \le (V_{in}$ or $V_{out}) \le V_{DD}$.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either V_{SS} or V_{DD}).

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ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	V_{DD} Vdc	−40°C Min	−40°C Max	25°C Min	25°C Typ	25°C Max	+85°C Min	+85°C Max	Unit
Supply Voltage	V_{DD}	–	4.75	5.25	4.75	5.0	5.25	4.75	5.25	V
Output Voltage "0" Level	V_{out}	5.0	–	0.05	–	0	0.05	–	0.05	V
Output Voltage "1" Level	V_{out}	5.0	4.95	–	4.95	5.0	–	4.95	–	V
Input Voltage (V_O = 4.5 or 0.5 V)	V_{IL}	5.0	–	1.5	–	2.25	1.5	–	1.5	V
(V_O = 0.5 or 4.5 Vdc)	V_{IH}	5.0	3.5	–	3.5	2.75	–	3.5	–	V
Output Drive Current (V_{OH} = 2.5 V) Source	I_{OH}	5.0	−0.23	–	−0.20	−1.7	–	−0.16	–	mA
(V_{OL} = 0.4 V) Sink	I_{OL}	5.0	0.23	–	0.20	0.78	–	0.16	–	mA
Input Current Pins 21, 22, 23	I_{in}	–	–	±0.1	–	±0.00001	±0.1	–	±1.0	μA
Pin 10	I_{in}	5.0	–	–	−1.5	–	−7.5	–	–	μA
Input Capacitance (V_{in} = 0)	C_{in}	–	–	–	–	5.0	–	–	–	pF
Quiescent Dissipation	P_Q	5.0	–	2.5	–	0.015	2.5	–	15	mW
Power Dissipation**† (Dynamic plus Quiescent) (C_L = 15 pF)	P_D	5.0	P_D = (7.5 mW/MHz) f + P_Q							mW
Output Rise Time** t_r = (3.0 ns/pF) C_L + 25 ns	t_{TLH}	5.0	–	–	–	70	200	–	–	ns
Output Fall Time** t_f = (1.5 ns/pF) C_L + 47 ns	t_{THL}	5.0	–	–	–	70	200	–	–	ns
Input Clock Frequency	f_{CL}	5.0	–	1.85	–	–	1.85	–	1.85	MHz
Clock Pulse Width	$t_{W(C)}$	–	200	–	200	–	–	200	–	ns
Reset Pulse Width	$t_{W(R)}$	–	500	–	500	–	–	500	–	ns

†For dissipation at different external capacitance (C_L) refer to corresponding formula:
$P_T(C_L = P_D + 2.6 \times 10^{-3}(C_L - 15\ pF)\ V_{DD}^2 f$
where: P_T, P_D in mW, C_L in pF, V_{DD} in Vdc, and f in MHz.
**The formula given is for the typical characteristics only.

TABLE 1 — OUTPUT CLOCK RATES

Rate Select B	Rate Select A	Rate
0	0	X1
0	1	X8
1	0	X16
1	1	X64

Output Number	Output Rates (Hz) X64	X16	X8	X1
F1	614.4 k	153.6 k	76.8 k	9600
F2	460.8 k	115.2 k	57.6 k	7200
F3	307.2 k	76.8 k	38.4 k	4800
F4	230.4 k	57.6 k	28.8 k	3600
F5	153.6 k	38.4 k	19.2 k	2400
F6	115.2 k	28.8 k	14.4 k	1800
F7	76.8 k	19.2 k	9600	1200
F8	38.4 k	9600	4800	600
F9	19.2 k	4800	2400	300
F10	12.8 k	3200	1600	200
F11	9600	2400	1200	150
F12	8613.2	2153.3	1076.6	134.5
F13	7035.5	1758.8	879.4	109.9
F14	4800	1200	600	75
F15	921.6 k	921.6 k	921.6 k	921.6 k
F16*	1.843 M	1.843 M	1.843 M	1.843 M

*F16 is buffered oscillator output.

FIGURE 1 — DYNAMIC SIGNAL WAVEFORMS

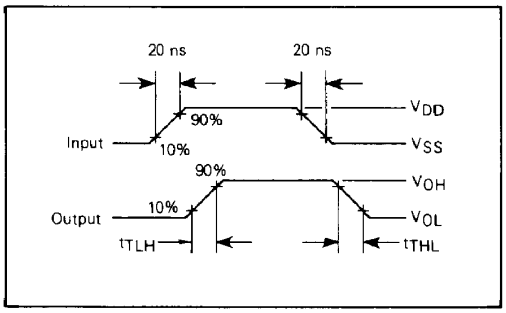
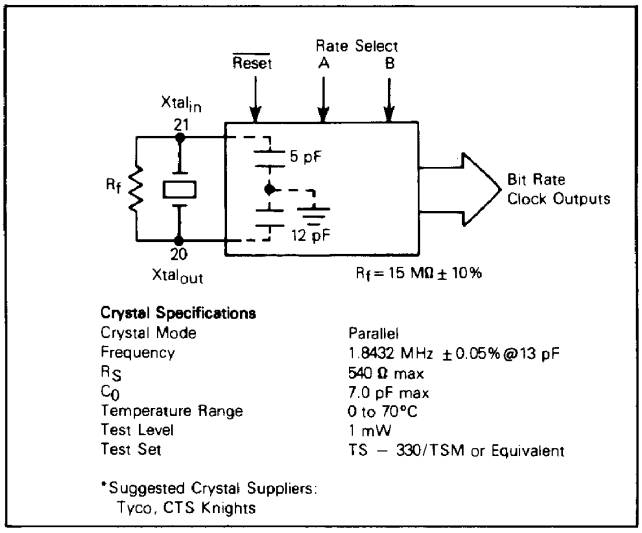


FIGURE 2 — TYPICAL CRYSTAL OSCILLATOR CIRCUIT



Crystal Specifications

Crystal Mode	Parallel
Frequency	1.8432 MHz ±0.05% @13 pF
R_S	540 Ω max
C_0	7.0 pF max
Temperature Range	0 to 70°C
Test Level	1 mW
Test Set	TS — 330/TSM or Equivalent

*Suggested Crystal Suppliers:
Tyco, CTS Knights

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